

800mA Dual-rail Very Low Dropout LDO

General Description

The ET551XX series are CMOS-based low-dropout, low-power linear regulators, offering 800mA with NMOS pass transistor and a separate bias supply voltage (VBIAS) . The device provides very stable, accurate output voltage with low noise, high ripple rejection and low supply current suitable for space constrained, noise sensitive application. The ET551XX series consist of an accurate voltage-reference block, an error amplifier, a thermal-shutdown circuit, and a current limit circuit.

The ET551XX series are available in the DFN4(1.2mm×1.2mm) or DFN6(1.2mm×1.2mm) package.

Features

- Wide VIN Input Voltage Range: 0.8V to 5.5V
 - Wide VBIAS Voltage Range: 2.4V to 5.5V
 - Output Voltage Range: 0.8V to 2.1V (Fixed)
0.8V to 3.6V (Externally set)
 - Very Low VBIAS Input Current of Typ. 80 μ A
 - Ultra Low Dropout: Typ. 200mV at 800mA, 1.1V Output, 3.3V Bias
 - Built-in Over Current Protection and Thermal Shutdown Circuit
 - Built-in Auto-discharging Circuit (optional)
 - Built-in Under Voltage Lock-out
 - Stable with a 2.2 μ F Ceramic Capacitor
 - Package: DFN4(1.2mm × 1.2mm × 0.4mm) or DFN6(1.2mm × 1.2mm × 0.4mm)
 - MSL: Level1

Applications

- Constant-voltage power supply for battery-powered device
 - Constant-voltage power supply for smartphones, tablets
 - Constant-voltage power supply for cameras, DVRs, STB and camcorders

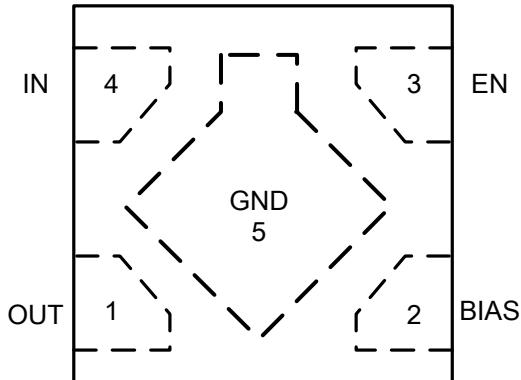
Device information

ET 551 XX X B

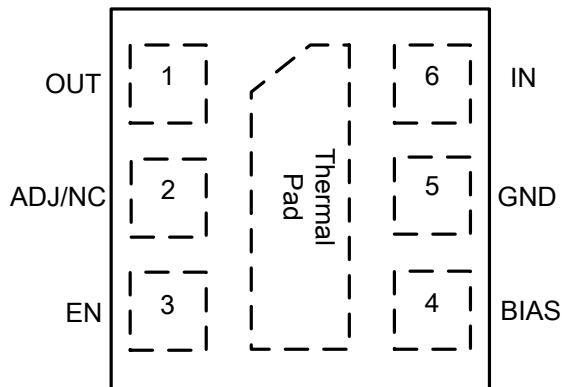
| <u>XX</u> Output Voltage | <u>X</u> Package | | <u>B</u> Auto-discharge Function | | |
|---------------------------------|-------------------------|----|---|---|----------------|
| Fixed | 0.8~2.1V | Y | DFN4 -1.2×1.2 | B | Auto-discharge |
| ADJ | 0.8~3.6V | Y1 | DFN6 -1.2×1.2 | / | None |

ET551XX

Pin Configuration



DFN4 (Top View)



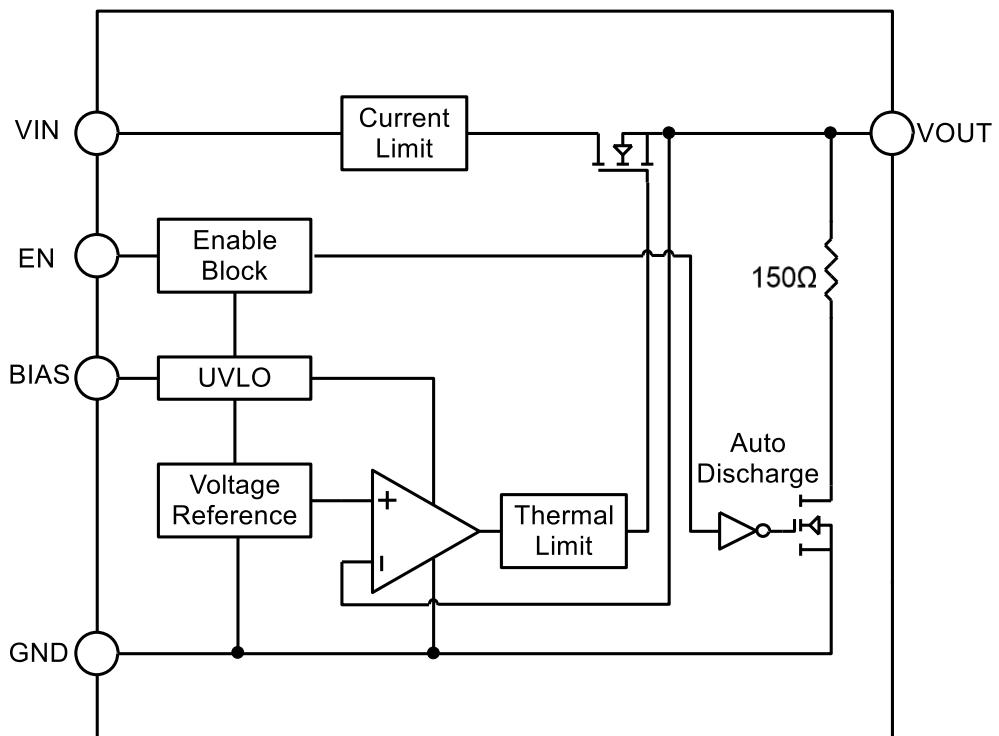
DFN6 (Top View)

Pin Function

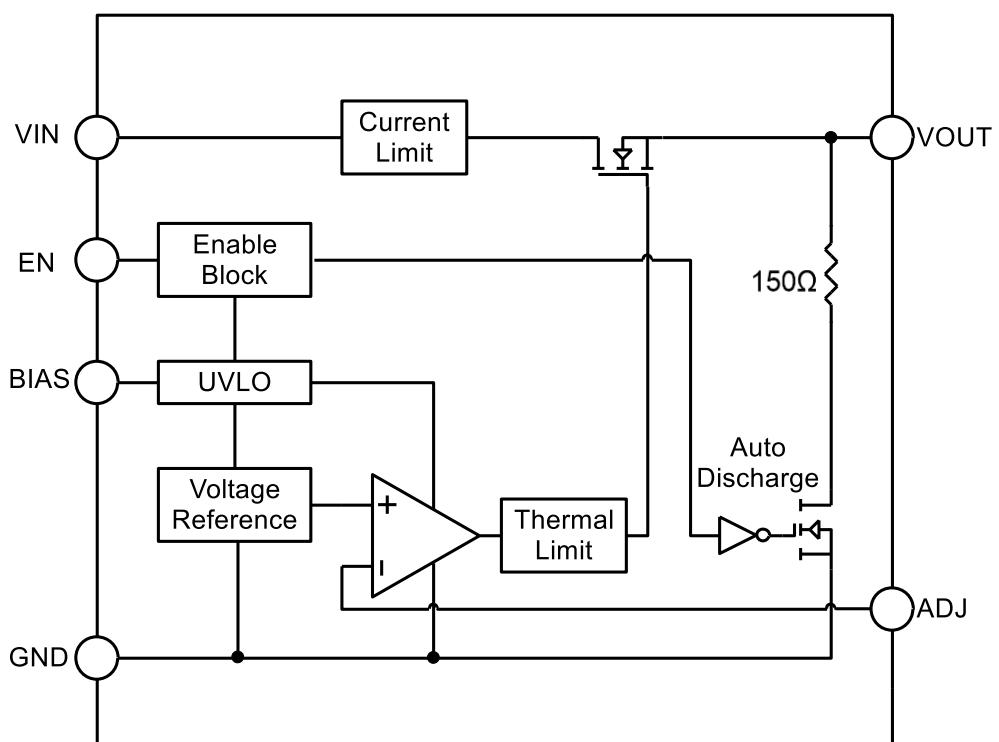
| Pin Name | | Symbol | Pin Description |
|----------|------|--------|---|
| DFN4 | DFN6 | | |
| 1 | 1 | OUT | The power output of the device. |
| 2 | 4 | BIAS | Input voltage for controlling circuit. |
| 3 | 3 | EN | Enable Input. |
| 4 | 6 | IN | Input voltage Pin. Large bulk capacitance should be placed closely to this pin. A 1µF ceramic capacitor is recommended at this pin. |
| 5 | 5 | GND | Ground pin. Thermal PAD. |
| | 2 | ADJ/NC | Adjustable Regulator Feedback Input. Connect to output voltage resistor divider central node. / No Connect. |

ET551XX

Block Diagram



Fixed Version



Adjustable Version

ET551XX

Functional Description

The ET551XX dual-rail very low dropout voltage regulator is using NMOS pass transistor for output voltage regulation from V_{IN} voltage. All the low current internal control circuitry is powered from the V_{BIAS} voltage.

The use of an NMOS pass transistor offers several advantages in applications. Unlike PMOS topology devices, the output capacitor has reduced impact on loop stability. V_{IN} to V_{OUT} operating voltage difference can be very low compared with standard PMOS regulators in very low V_{IN} applications.

The ET551XX offers smooth monotonic start-up.

Input and output Capacitor

The device is designed to be stable for ceramic output capacitors with Effective capacitance in the range from $2.2\mu F$ to $4.7\mu F$. The device is also stable with multiple capacitors in parallel, having the total effective capacitance in the specified range. In applications where no low input supplies impedance available (PCB inductance in V_{IN} and/or V_{BIAS} inputs as example), the recommended $C_{IN} = 1\mu F$ and $C_{BIAS} = 0.1\mu F$ or greater.

Enable Pin Operation

The ET551XX is turned on by setting the EN pin to "H". The threshold limits are covered in the electrical characteristics table in this datasheet. When the EN pin is not used, connect the EN pin with V_{BIAS} to keep the LDO in operating mode.

Current Limit Protection

When output current of V_{OUT} pin is higher than current limit threshold or the V_{OUT} pin is direct short to GND, the current limit protection will be triggered and clamp the output current at a predesigned level to prevent over-current and thermal damage.

Thermal Shutdown Protection

Thermal protection disables the output when the junction temperature rises to approximately $+165^{\circ}C$, allowing the device to cool down. When the junction temperature reduces to approximately $+145^{\circ}C$ the output circuit is enabled again. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the heat dissipation of the regulator, protecting it from damage due to overheating.

Auto Discharging

When the EN pin set to "L", the output circuit will be disable immediately, and the Auto-Discharging circuit will be turned on to discharge the electric charge on output capacitor, and decrease the voltage of V_{OUT} in very short time. The Auto-Discharging function is optional.

Output Voltage Adjust(Only for ADJ Version)

The required output voltage of Adjustable devices can be adjusted from V_{REF} to 3.6 V using two external resistors. Typical application schematics is shown blow.

$$V_{OUT} = V_{REF} \times (1 + R1/R2)$$

ET551XX

Typical value of V_{REF} is 0.8V. It is recommended to keep the total serial resistance of resistors (R_1+R_2) not greater than 100K Ω .

The output voltage needs to take into account the error caused by the resistance accuracy.

Absolute Maximum Ratings

| Item | Rating | Unit |
|--------------------------------|-------------|------|
| Input Voltage(VIN Pin) | -0.3 to 6.0 | V |
| Input Voltage (VBIAS Pin) | -0.3 to 6.0 | V |
| Input Voltage (EN Pin) | -0.3 to 6.0 | V |
| Input Voltage (ADJ Pin) | -0.3 to 6.0 | V |
| Output Voltage | -0.3 to 6.0 | V |
| Maximum Load Current | 800 | mA |
| Maximum Power Consumption | 640 | mW |
| Storage Temperature Range | -65 to +150 | °C |
| Operating Junction Temperature | -40 to +150 | °C |
| ESD HBM | 4000 | V |
| ESD CDM | 1500 | V |

Recommended Operating Conditions

| Symbol | Item | Rating | Unit |
|------------|---|--|-----------|
| V_{IN} | IN Input Voltage | $V_{OUT} + V_{DROP}$ to 5.5 | V |
| V_{BIAS} | BIAS Input Voltage | 2.7 to 5.5 & $V_{BIAS} \geq V_{OUT} + 1.4V$ | V |
| I_{OUT} | Output Current | 0 to 800 | mA |
| T_A | Operating Ambient Temperature | -40 to 85 | °C |
| C_{IN} | Effective Input Ceramic Capacitor Value | 0.47 to 10 | μF |
| C_{BIAS} | Effective Input Ceramic Capacitor Value | 0.047 to 4.7 | μF |
| C_{OUT} | Effective Output Ceramic Capacitor Value | 1 to 10 | μF |
| ESR | Input and Output Capacitor Equivalent Series Resistance | 5 to 100 | $m\Omega$ |

ET551XX

Electrical Characteristics

(Unless otherwise noted , $V_{IN}=V_{OUT}+0.3V$, $V_{BIAS}=V_{OUT}+1.6V$, $I_{OUT}=1mA$, $C_{IN}=1\mu F$, $C_{OUT}=2.2\mu F$, $C_{BIAS}=0.1\mu F$, $T_A= -40^{\circ}C \sim 85^{\circ}C$.Typical values are at. $T_A=25^{\circ}C$)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--|-------------------|---|--------------------------|--------------------------|------|------------|
| Input Voltage Range | $V_{IN}^{(1)}$ | $V_{IN}>V_{OUT}$ | $V_{OUT}+$ V_{DROP} | | 5.5 | V |
| V_{BIAS} Voltage Range | V_{BIAS} | $V_{BIAS}\geq V_{OUT}+1.6V$ | 2.4 | | 5.5 | V |
| Under-voltage lock-out | V_{UVLO} | V_{BIAS} Rising/Hysteresis | | 1.6/0.2 | | V |
| V_{BIAS} Current | $I_{Q_ON}^{(4)}$ | Active mode: $V_{EN}=H$ | | 80 | 110 | μA |
| | I_{Q_OFF} | $V_{EN}=L$ | | 0.5 | 1.0 | μA |
| Output Voltage | V_{OUT} | $I_{OUT}=1mA \sim 800mA$, $T_A=25^{\circ}C$ | -2 | | 2 | % |
| Dropout Voltage | $V_{DROP}^{(2)}$ | $I_{OUT}=500mA, V_{OUT}=1.1V$ | | 125 | 187 | mV |
| | | $I_{OUT}=800mA, V_{OUT}=1.1V$ | | 200 | 300 | |
| Current Limit | I_{LIM} | $V_{OUT}=90\%V_{OUT}$ | 800 | 1150 | 1550 | mA |
| Load Regulation | Reg_{LOAD} | $1mA \leq I_{OUT} \leq 800mA$ | | 2 | 20 | mV |
| V_{IN} Line Regulation | Reg_{LINE} | $V_{OUT}+0.3V \leq V_{IN} \leq 5V$ ($I_{OUT}=1mA$) | | 0.01 | 0.1 | %/V |
| V_{BIAS} Line Regulation | | $(V_{OUT}+1.6V) < V_{BIAS} < 5.5V$, ($V_{IN}=V_{OUT}+0.3V$, $I_{OUT}=1mA$) | | 0.01 | 0.1 | %/V |
| Ripple Rejection | $PSRR^{(3)}$ | V_{IN} to V_{OUT} , $f=1kHz$, Ripple 0.2Vp-p, $I_{OUT}=30mA$ | | 80 | | dB |
| | | V_{BIAS} to V_{OUT} , $f=1kHz$, Ripple 0.2Vp-p, $I_{OUT}=30mA$ | | 80 | | |
| Output Noise | $e_N^{(3)}$ | $V_{IN}=1.6V, V_{OUT}=1.1V$, $f= 10 Hz$ to $100 kHz$ | | $50 \times$ V_{OUT} | | $\mu VRMS$ |
| EN Pull-down Current | I_{EN} | $V_{EN}=5.5V$ | | 0.5 | 1 | μA |
| EN Input Voltage High | V_{ENH} | | 0.9 | | | V |
| EN Input Voltage Low | V_{ENL} | | | | 0.4 | V |
| Output resistance of auto discharge at off state | R_{DIS} | $V_{EN}=0V, V_{OUT}=0.5V$ | | 150 | | Ω |
| Line transient | $V_{TRLN}^{(3)}$ | $V_{IN}=V_{OUT}+0.3V$ to $5.5V$ in $10\mu s$, $I_{OUT}=1mA, T_A=25^{\circ}C$ | | 18 | 30 | mV |
| | | $V_{IN}= 5.5V$ to $V_{OUT}+0.3V$ in $10\mu s$, $I_{OUT}=1mA, T_A=25^{\circ}C$ | | 18 | 30 | mV |
| Load transient | $V_{TRLD}^{(3)}$ | $I_{OUT}=1mA$ to $800mA$ in $10\mu s$ $V_{IN}=V_{OUT}+0.5V, T_A=25^{\circ}C$ | | 120 | 180 | mV |
| | | $I_{OUT}=800mA$ to $1mA$ in $10\mu s$ $V_{IN}=V_{OUT}+0.5V, T_A=25^{\circ}C$ | | 80 | 120 | mV |

ET551XX

Electrical Characteristics(Continued)

(Unless otherwise noted , $V_{IN}=V_{OUT}+0.3V$, $V_{BIAS}=V_{OUT}+1.6V$, $I_{OUT}=1mA$, $C_{IN}=1\mu F$, $C_{OUT}=2.2\mu F$, $C_{BIAS}=0.1\mu F$, $T_A= -40^{\circ}C \sim 85^{\circ}C$.Typical values are at. $T_A=25^{\circ}C$)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---------------------------------------|-----------------|---|-----|-----|-----|-------------|
| Turn-On Time | T_{ON} | From assertion of V_{EN} to $V_{OUT}=98\%V_{OUT(NOM)}$ | | 120 | | μs |
| Thermal Shutdown Temperature | $T_{TSD}^{(3)}$ | Temperature increasing | | 165 | | $^{\circ}C$ |
| Thermal Shutdown Released Temperature | $T_{TSR}^{(3)}$ | Temperature decreasing | | 145 | | $^{\circ}C$ |

Notes:

1:The maximum input voltage should take into account the maximum power consumption ($P_{D(MAX)}$).The calculation formula is as follows:

$$P_{D(MAX)} = (V_{IN(MAX)} - V_{OUT}) \times I_{OUT}$$

The maximum power consumption of the circuit is 640mW.

$$V_{IN(MAX)} = 640mW / I_{OUT} + V_{OUT}$$

For example:

If $V_{OUT}= 1.1V$, $I_{OUT}=800mA$, The maximum input voltage is $V_{IN(MAX)}=640mW / 800mA+1.1=1.9V$

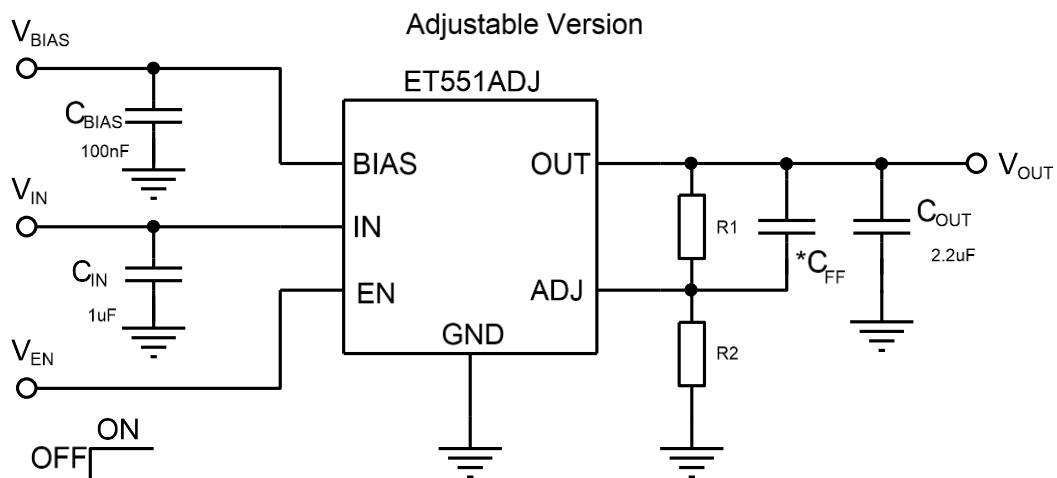
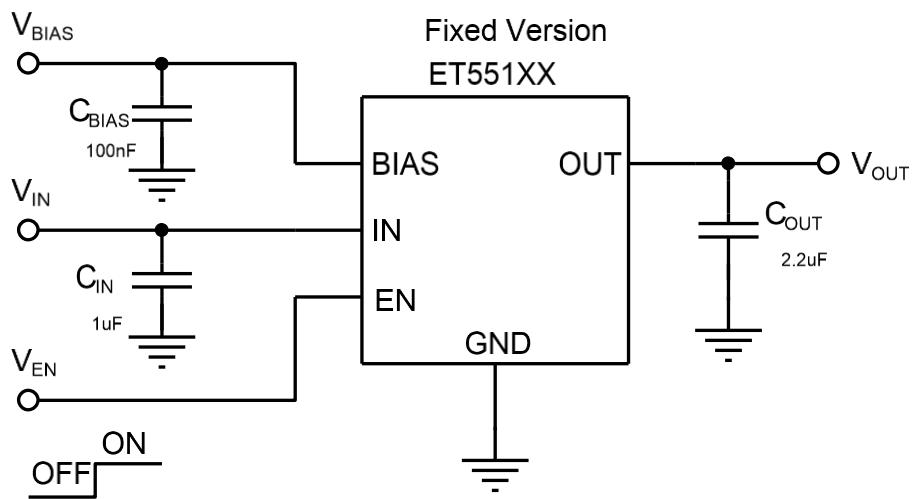
2: V_{DROP} FT test method: test the V_{OUT} voltage at $V_{SET} + V_{DROP MAX}$ with output current.

3: Guaranteed by design and characterization. not a FT item.

4: Since the power on process of BIAS needs a large current, the BIAS input voltage should have a current driving capacity of more than 120mA.

ET551XX

Application Circuits



Note*: Adjust Version: $V_{OUT} = 0.8 \times (1 + R1/R2)$, (R1+R2) no greater than 100kΩ.

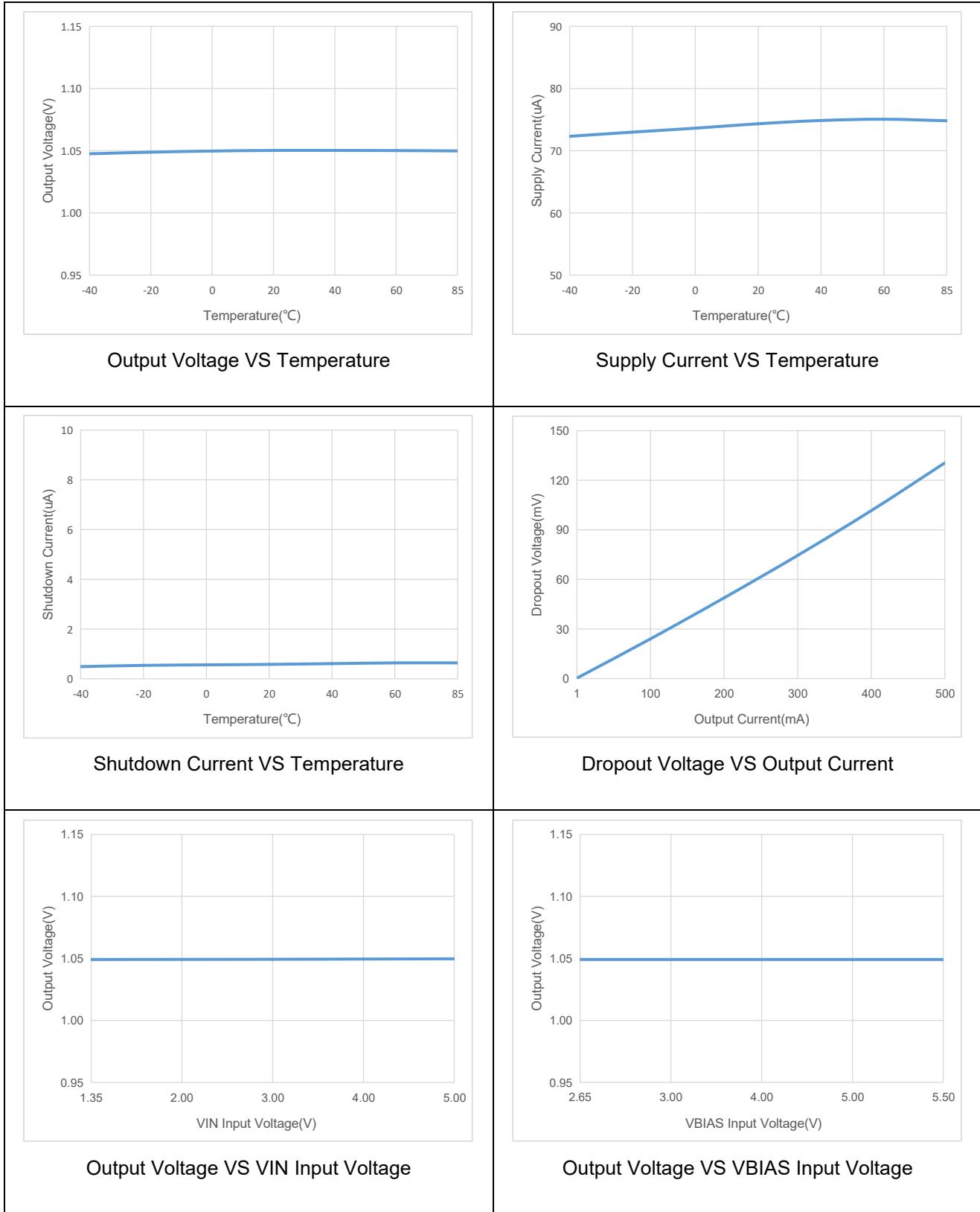
The feedforward capacitor CFF is optional for the optimization of transient response.

If BIAS input series resistor is used, it is recommended no greater than 20Ω.

ET551XX

Typical Characteristics

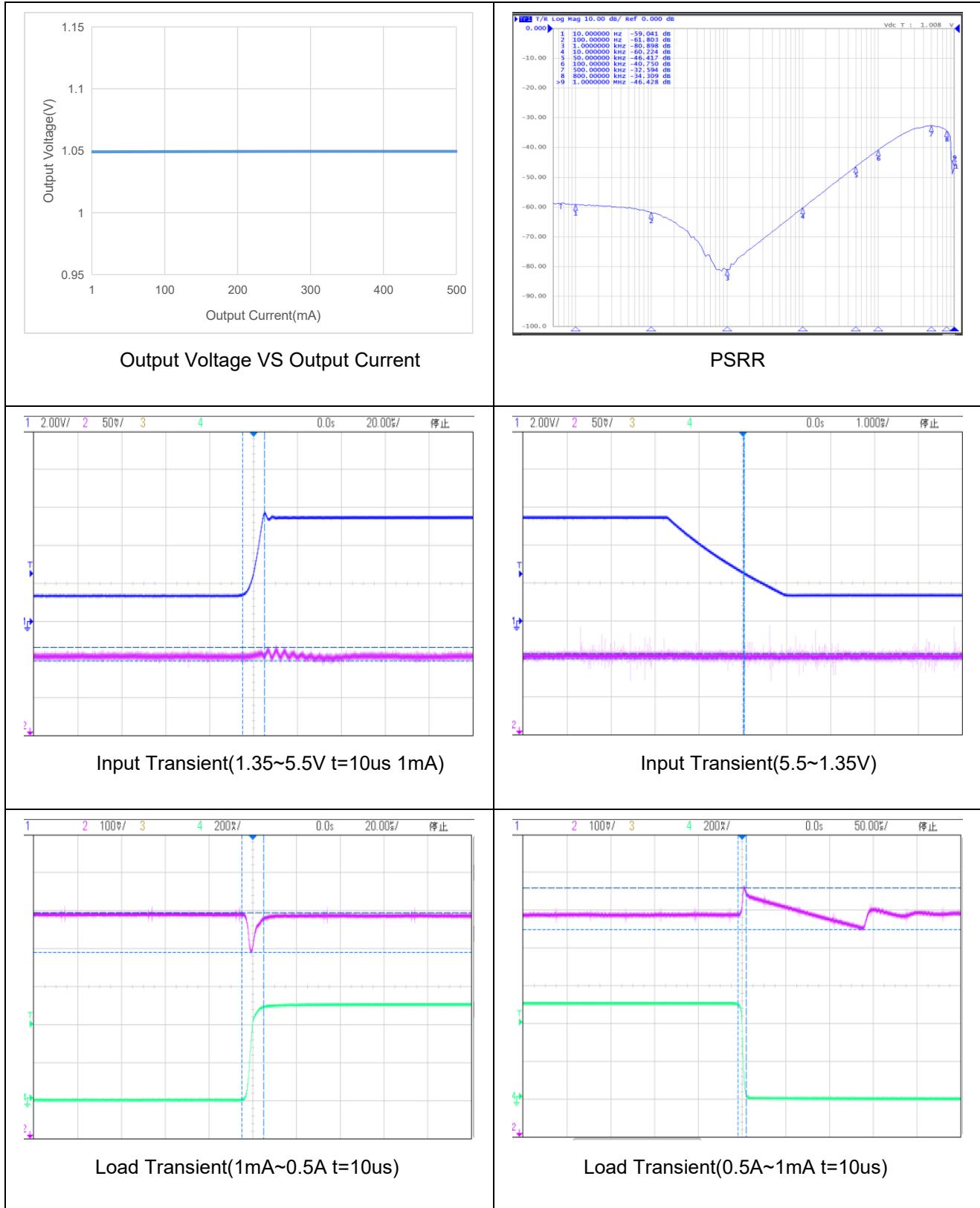
($V_{OUT}=1.05V$, $V_{IN}=V_{OUT}+0.3V$, $V_{BIAS}=V_{OUT}+1.6V$, $C_{IN}=1\mu F$, $C_{OUT}=2.2\mu F$, $C_{BIAS}=1\mu F$, $T_A= -40^{\circ}C \sim +85^{\circ}C$)



ET551XX

Typical Characteristics(Continued)

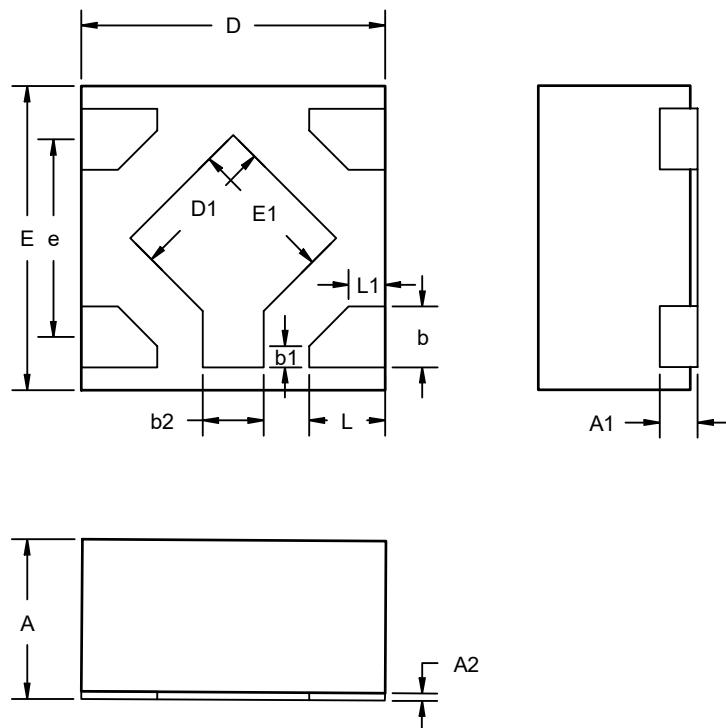
($V_{OUT}=1.05V$, $V_{IN}=V_{OUT}+0.3V$, $V_{BIAS}=V_{OUT}+1.6V$, $C_{IN}=1\mu F$, $C_{OUT}=2.2\mu F$, $C_{BIAS}=1\mu F$, $T_A = -40^{\circ}C \sim +85^{\circ}C$)



ET551XX

Package Dimension

DFN4(1.2x1.2)

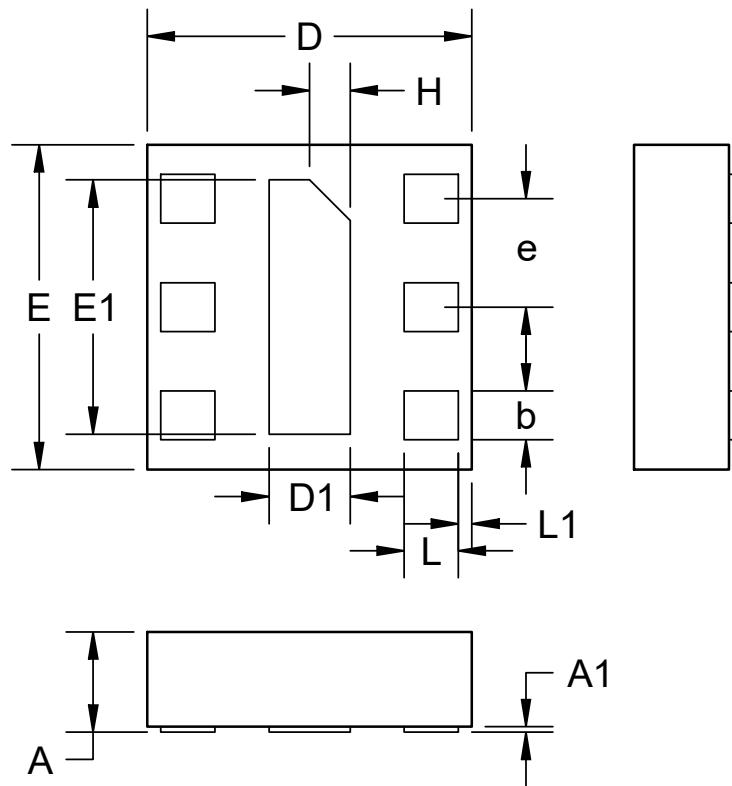


COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

| SYMBOL | MIN | NOM | MAX |
|--------|---------|------|------|
| A | 0.35 | 0.40 | 0.45 |
| A1 | 0.13REF | | |
| A2 | 0.00 | 0.02 | 0.05 |
| b | 0.25 | 0.30 | 0.35 |
| b1 | 0.12REF | | |
| b2 | 0.15 | 0.20 | 0.25 |
| D | 1.15 | 1.20 | 1.25 |
| D1 | 0.58 | 0.63 | 0.68 |
| E | 1.15 | 1.20 | 1.25 |
| E1 | 0.58 | 0.63 | 0.68 |
| e | 0.8BSC | | |
| L | 0.25 | 0.30 | 0.35 |
| L1 | 0.12REF | | |

ET551XX

DFN6(1.2x1.2)

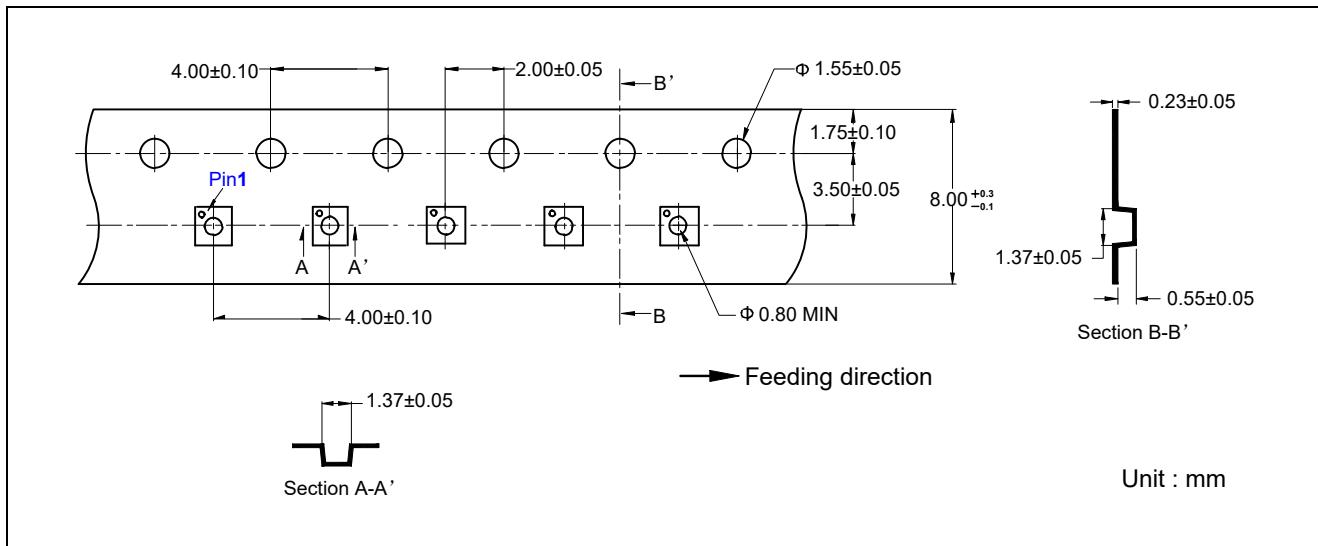


COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

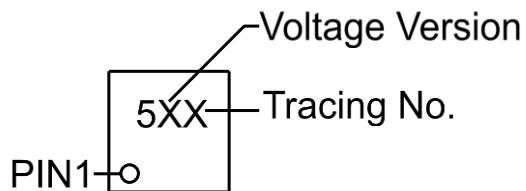
| SYMBOL | MIN | NOM | MAX |
|--------|---------|------|------|
| A | 0.34 | 0.37 | 0.50 |
| A1 | 0 | 0.02 | 0.05 |
| b | 0.13 | 0.18 | 0.23 |
| D | 1.10 | 1.20 | 1.30 |
| D1 | 0.25 | 0.30 | 0.35 |
| E | 1.10 | 1.20 | 1.30 |
| E1 | 0.89 | 0.94 | 0.99 |
| e | 0.30 | 0.40 | 0.50 |
| L | 0.15 | 0.20 | 0.25 |
| L1 | 0 | 0.05 | 0.10 |
| H | 0.15REF | | |

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Reel



Marking Information



| <u>X</u> Voltage Version | <u>X</u> |
|--------------------------|----------|
| A | 1.2V |
| I | 1.1V |
| U | 1.05V |
| 5 | ADJ |

Tracing Number

ET551XX

Revision History and Checking Table

| Version | Date | Revision Item | Modifier | Function & Spec Checking | Package & Tape Checking |
|---------|------------|--|---------------|--------------------------|-------------------------|
| 1.0 | 2018-10-15 | Preliminary Version | Liu Zhen Chao | Zhu Jun Li | Zhu Jun Li |
| 1.1 | 2019-02-27 | Add TTSD&TTSR in EC table , revise test condition of ILIM, revise the functional description | Liuyg | Liujy | Liujy |
| 1.2 | 2019-04-04 | Up to 800mA | Liuyg | Liujy | Liujy |
| 1.3 | 2022-09-03 | Update Typeset | Tu Guo Zhu | Liuyg | Liujy |
| 1.4 | 2023-7-19 | BIAS current add note ,thickness | Shi bo | Liuyg | Liujy |